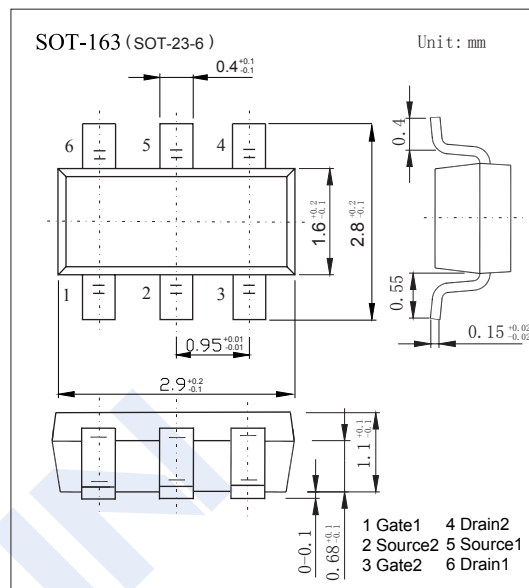
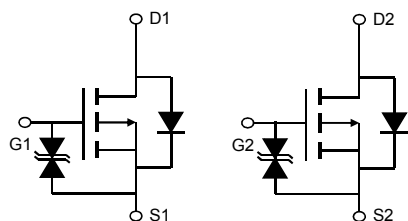


Dual P-Channel MOSFET

AO6801E (KO6801E)

■ Features

- $V_{DS} (V) \approx -30V$
- $I_D \approx -2A$ ($V_{GS} \approx -10V$)
- $R_{DS(ON)} < 110m\Omega$ ($V_{GS} \approx -10V$)
- $R_{DS(ON)} < 135m\Omega$ ($V_{GS} \approx -4.5V$)
- $R_{DS(ON)} < 185m\Omega$ ($V_{GS} \approx -2.5V$)
- ESD Rating: 2000V HBM

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	± 12	
Continuous Drain Current	$T_A = 25^\circ C$	I_D	-2	A
	$T_A = 70^\circ C$		-1.6	
Pulsed Drain Current		I_{DM}	-15	
Power Dissipation	$T_A = 25^\circ C$	P_D	0.7	W
	$T_A = 70^\circ C$		0.45	
Thermal Resistance.Junction- to-Ambient	$t \leq 10s$	R_{thJA}	180	$^\circ C/W$
	Steady-State		230	
Thermal Resistance.Junction- to-Lead		R_{thJL}	180	
Junction Temperature		T_J	150	$^\circ C$
Junction Storage Temperature Range		T_{stg}	-55 to 150	

Dual P-Channel MOSFET

AO6801E (KO6801E)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =-250 μA, V _{GS} =0V	-30			V
Gate-Source breakdown voltage	BV _{GSO}	V _D =0V, I _G =±250μA	±12			
Zero Gate Voltage Drain Current	I _{DSS}	V _D =-30V, V _{GS} =0V			-1	μA
		V _D =-30V, V _{GS} =0V, T _J =55°C			-5	
Gate-Body leakage current	I _{GSS}	V _D =0V, V _{GS} =±12V			±10	μA
Gate Threshold Voltage	V _{GS(th)}	V _D =V _{GS} , I _D =-250 μA	-0.7		-1.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-2A			110	mΩ
		V _{GS} =-10V, I _D =-2A T _J =125°C			158	
		V _{GS} =-4.5V, I _D =-1.5A			135	
		V _{GS} =-2.5V, I _D =-1A			185	
On state drain current	I _{D(ON)}	V _{GS} =-10V, V _D =-5V	-15			A
Forward Transconductance	g _{FS}	V _D =-5V, I _D =-2A		7		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _D =-15V, f=1MHz		305		pF
Output Capacitance	C _{oss}			42		
Reverse Transfer Capacitance	C _{rss}			26		
Gate resistance	R _g	V _{GS} =0V, V _D =0V, f=1MHz		8.5	17	Ω
Total Gate Charge (10V)	Q _g	V _{GS} =-10V, V _D =-15V, I _D =-2A		7	12	nC
Total Gate Charge (4.5V)				3.5	6	
Gate Source Charge	Q _{gs}			0.7		
Gate Drain Charge	Q _{gd}			1.2		
Turn-On DelayTime	t _{d(on)}	V _{GS} =-10V, V _D =-15V, R _L =7.5Ω, R _{GEN} =3Ω		6		ns
Turn-On Rise Time	t _r			4		
Turn-Off DelayTime	t _{d(off)}			23		
Turn-Off Fall Time	t _f			7		
Body Diode Reverse Recovery Time	t _{rr}	I _F =-2A, dI/dt=500A/μs		9.5		nC
Body Diode Reverse Recovery Charge	Q _{rr}			13.5		
Maximum Body-Diode Continuous Current	I _S				-1	A
Diode Forward Voltage	V _{SD}	I _S =-1A, V _{GS} =0V			-1	V

* The static characteristics in Figures 1 to 6 are obtained using <300us pulses, duty cycle 0.5% max.

■ Marking

Marking	V1**
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Dual P-Channel MOSFET

AO6801E (KO6801E)

■ Typical Characteristics

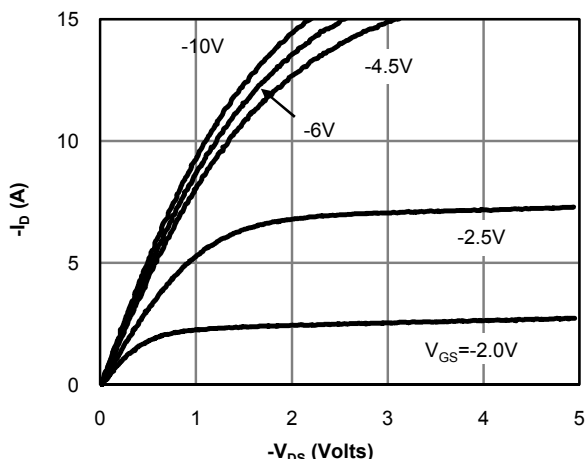


Fig 1: On-Region Characteristics (Note E)

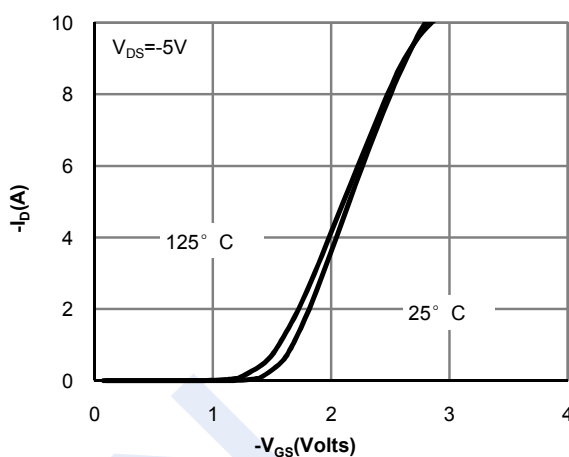


Figure 2: Transfer Characteristics (Note E)

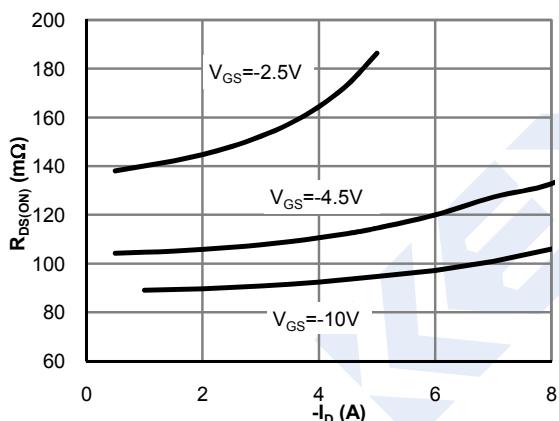


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

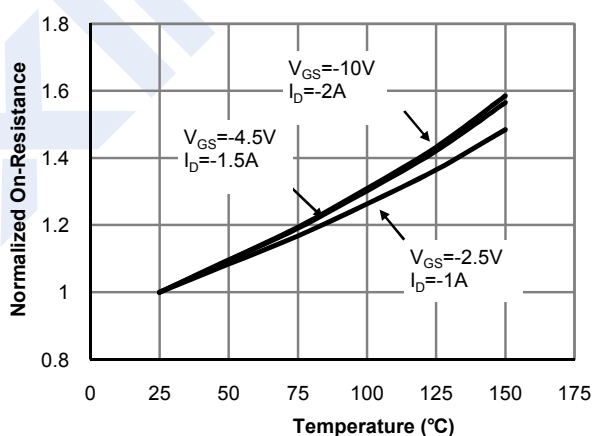


Figure 4: On-Resistance vs. Junction Temperature (Note E)

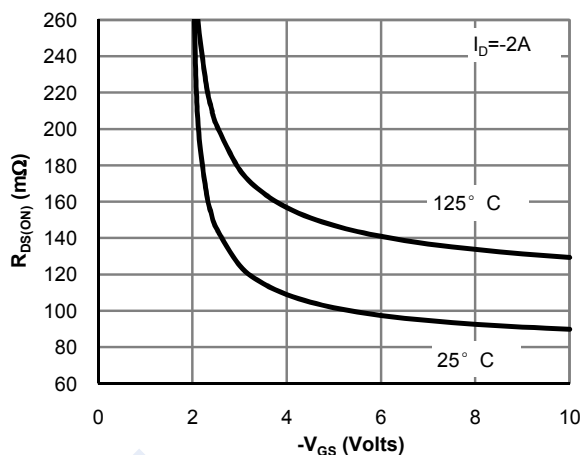


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

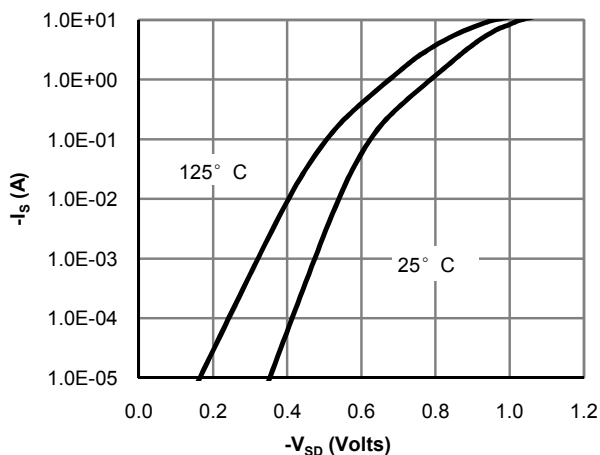


Figure 6: Body-Diode Characteristics (Note E)

Dual P-Channel MOSFET

AO6801E (KO6801E)

■ Typical Characteristics

